IN THE SPECIFICATION

Please replace the title with the following:

"METHOD FOR PRODUCING ULTRA-THIN SEMICONDUCTOR DEVICE"

Please amend the last paragraph on page 23 as follows:

Below, an explanation will be given of embodiments of a method ~~of production and a production~~ and apparatus ~~of~~ for producing a back-illuminated solid-state image pickup device, and ~~of a single-surface resin sealed ultra-thin chip size hollow package according to~~ a method of ~~production of~~ producing an ultra-thin SOI substrate, according to ~~of~~ the present invention ~~with reference to the drawings~~.

Please amend the first paragraph on page 24 as follows:

In the ~~present~~ first embodiment, ~~the~~ an explanation will be given of a method ~~of production and production~~ and apparatus ~~of~~ for producing a back-illuminated solid-state image pickup device of a single-surface resin sealed ultra-thin chip size hollow package using ~~the~~ a double porous layer separation method (for example the method of separating a seed substrate by a first porous Si layer formed on a seed substrate and separating the support substrate by a second porous Si layer formed on the support substrate) ~~among the methods of fabrication of new ultra-thin SOI substrates~~.

Please amend the second paragraph on page 29, beginning on line 8, as follows:

Next, by anodic conversion in the same way as ~~the~~ discussed above, ~~for example a~~ mixture obtained by mixing 50% hydrogen fluoride solution and ethyl

alcohol at a volume ratio of 2:1 ~~is~~ may be used as the electrolytic solution and circulated for about 5 minutes at a current density of 10 mA/cm^2 to change the high concentration p-type impurity layer to a low porous Si layer of a low porosity, and to change the low concentration p-type impurity layer to a high porous Si layer of a high porosity. By this, as shown in FIG. 1B, the support substrate 20 is formed with a porous Si layer 21 comprising a low porous Si layer 21a of a low porosity having a thickness of about 10 μm, a high porous Si layer 21b of a high porosity having a thickness of about 2 μm, and a low porous Si layer 21c of a low porosity having a thickness of about 10 μm.

Please amend the paragraph beginning on page 32, line 24, and ending on page 33, line 9, as follows:

It is ~~necessary~~ preferable to set the thickness of the first semiconductor layer 12 for the device fabrication to a thickness of about 5 to 20 μm since sensitivity with respect to the incident light for the back-illuminated is necessary desired. Further, the second semiconductor layer 22 and the low porous Si layer 21c are removed in the end as will be explained later and thereby an air gap (height) is defined between the seal glass and the incident surface, so the total thickness of the second semiconductor layer 22 and the low porous Si layer 21c preferably becomes about 10 to 50 μm.

Please amend the second paragraph on page 57 beginning at line 13 as follows:

In the ~~present~~ second embodiment, ~~the~~ explanation will be given of [[a]] an alternative method ~~of production and production~~ and apparatus for production of a back-illuminated solid-state image pickup device of a single-surface resin sealed

ultra-thin chip size hollow package using ~~the~~ a double ion implanted layer separation method (the method of separating a seed substrate by a first ion implanted layer formed by implanting for example hydrogen atoms in the seed substrate and separating the support substrate by a second ion implanted layer formed by implanting for example hydrogen in the support substrate) ~~among the methods of fabrication of new ultra-thin SOI substrates~~.

Please amend the first full paragraph on page 61 beginning at line 11 as follows:

Note that, the peeled off seed substrate can be reused. Note that, in the same way as ~~the~~ discussed above, it is also possible to separate this from the ion implanted layer by lasering.

Please amend the paragraph beginning at page 70, line 24 and continuing to page 71, line 11 as follows:

In the ~~present~~ third embodiment, ~~the~~ explanation will be given of a method ~~of production and production~~ and apparatus for the production of a back-illuminated solid-state image pickup device of a single-surface resin sealed ultra-thin chip size hollow package using the porous layer/ion implanted layer separation method combining the porous layer separation method and ion implanted layer separation method described above (the method of separating a seed substrate by an ion implanted layer formed by implanting hydrogen atoms in the seed substrate and separating the support substrate by a porous Si layer formed on the support substrate) ~~among the methods of fabrication of new ultra-thin SOI substrates~~.

Please amend the paragraph beginning at page 75, line 25 and continuing to page 76, line 10 as follows:

By proceeding through the following steps of ~~the step of~~ device formation (step 6), ~~the step of~~ forming the score and resin protective film (step 7), ~~the step of~~ separating the support substrate (step 8), ~~the step of~~ fabrication of the back-illuminated solid-state image pickup device chip (step 9), ~~the step of~~ affixing the transparent substrate (step 10) and ~~the step of~~ mounting to the mounting board (step 11) explained in the first embodiment, an ultra-thin back-illuminated solid-state image pickup device of a single-surface resin sealed chip size hollow package as shown in FIG. 9B is produced.